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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): K. OHNISHI et al

Serial No.: 09/829,969

Filed: April 11, 2001

For: SEMICONDUCTOR DEVICE AND PROCESS FOR
PRODUCING THE SAME

Group: 2818

Examiner: M. TRAN

AMENDMENT

MS: AMENDMENTS (Fee)

Commissioner For Patents
POB 1450
Alexandria, VA 22313-1450

June 6, 2003

RECEIVED
JUN 11 2003
TECHNOLOGY CENTER 2800

Sir:

In response to the Office Action dated February 10, 2003, the period of response for which extension of time is requested in the attached Petition for Extension of Time, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE CLAIMS:

Please amend claims 1, 4, 5, 8, 25, 28, 29, 31 and 33 to read as follows:

1. (Twice Amended) A semiconductor device with an MOS transistor, wherein a gate electrode of the MOS transistor is provided as a stacked structure comprising a silicon layer, a metal silicide layer, a metal nitride layer and a metallic layer, formed